

**Amendments to the Claims:**

This listing of claims will replace all prior versions, and listings, of claims in the application.

**Listing of Claims:**

Claims 1-8 (canceled)

Claim 9 (currently amended): A method of forming an integrated circuit capacitor comprising:

providing a silicon substrate with a first dielectric film containing at least one copper layer;

forming a ~~second dielectric~~ etch-stop/barrier layer over said first dielectric layer and said copper layer wherein said ~~second dielectric~~ etch-stop/barrier layer contacts said copper layer;

forming a first conductive layer over said first dielectric layer wherein said first conductive layer contacts said etch-stop/barrier dielectric layer; and

removing a region of said first conductive layer such that a portion of said ~~second dielectric~~ etch-stop/barrier layer remains between said first conductive layer and said copper layer wherein said first conductive layer, said ~~second dielectric~~ etch-stop/barrier layer, and said copper layer form a capacitor.

Claim 10 (original): The method of claim 9 further comprising:

forming copper contacts to said first conductive layer; and

forming a second copper layer that electrically contacts said copper contacts.

Claim 11 (original): The method of claim 9 wherein said first conductive layer is formed from a material selected from the group consisting of aluminum, aluminum oxide,

tantalum nitride, titanium nitride, tungsten, tungsten nitride, silicon carbide, and their alloys.

Claim 12 (currently amended): The method of claim 9 wherein said ~~second dielectric etch-stop/barrier~~ layer is formed using at least two different dielectric films.

Claim 13 (canceled)

Claim 14 (currently amended): The method of claim 9 wherein said ~~second dielectric etch-stop barrier~~ layer is silicon nitride.

Claims 15-17 (canceled)

**Amendments to the Drawings:**

None